



5 é / Descriptions

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□ª / Features

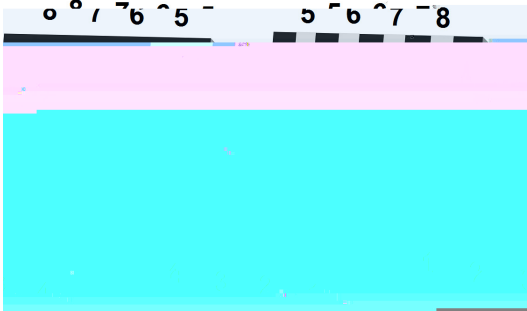
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Ð ÷ / Applications

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- ÚZ 6 OT 4[SHKX6 OT 4GSK	- df VDD	- a ¢ 6 OT *KYIXOVZOUT
	- 4 * < 3	> € / ìª kN P / ¿ â

3. Absolute Maximum Ratings(Ta=25℃ ;)

@ f/Parameter	... Z/Symbol	f > /Value	% y/Unit
V _{DD} input pin voltage	V _{IN}	-0.3 to +8	V
V _{VM} input pin voltage	V _{VM}	-8 to +10	V
Maximum Junction Temperature	T _J	-40 to +145	
Storage Temperature	T _{stg}	-55 to +145	
ESD g HBM Mode h	ESD	f 4000	V

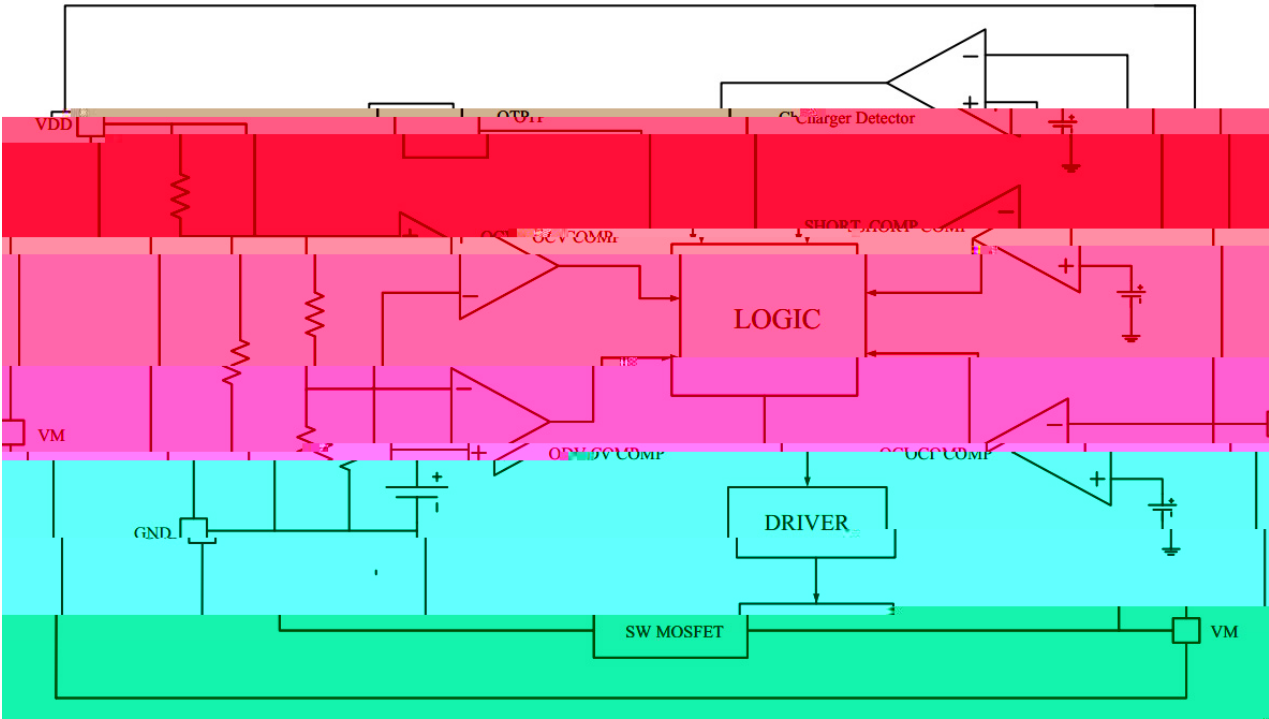
4. Electrical Characteristics(Unless otherwise specified,Ta=25℃ ;)

@ f Parameter	... Z Symbol	y i Ú ^ Test Condition	Â 4 > Min	Á ° > Typ	Â Ý > Max	% y Unit
Power supply						
Supply Voltage	V _{DD}		0		6	V
Charger input voltage	V _M		-6		6	V
Detection voltage						
Overcharge Detection Voltage	V _{OCV}		4.25	4.3	4.35	V
Overcharge Release Voltage	V _{OCR}		4.04	4.10	4.16	V
Overdischarge Detection Voltage	V _{ODV}		2.30	2.40	2.50	V
Overdischarge Release Voltage	V _{ODR}		2.90	3.00	3.10	V
Detection current						
Overdischarge Current Detection	I _{OCI}		9	11.5	14	A
Load Short-Circuiting Detection	I _{SHORT}		15	25	35	A
Overcharge Current Detection	I _{CHA}		7	10	13	A
Static current						
Current Consumption in Normal Operation	I _{OPe}	V _M =0V		3.5	7	A
Current Consumption in Dormancy	I _{PDN}	V _{DD} =1.8V		0.6	1.5	A
Pull-up and Pull-down Current from VM						
Internal pull-up current	I _{PU}			14		A
Internal pull-down current	I _{PD}	V _M =1V		14		A
Equivalent FET on Resistance						
Equivalent FET on Resistance	R _{DS}	I _{VM} =1A	12.5	16	18	m

Electrical Characteristics(Ta=25 ;)

@ f Parameter	... Z Symbol	y i Ú ^ Test Condition	Â 4 > Min	Á ° > Typ	Â Ý > Max	% y Unit
Over temperature protection						
Over-temperature protection	OTP			145		
Over-temperature protection release temperature	OTPR			120		
Detection delay						
Overcharge Voltage Detection Delay Time	T _{OCV}			100		ms
Overdischarge Voltage Detection Delay Time	T _{ODV}			100		ms
Overdischarge Current1 Detection Delay Time	T _{IOV1}			8		ms
Overdischarge Current2 Detection Delay Time	T _{IOV2}			2		ms
Load Short-Circuiting Detection Delay Time	T _{SHORT}			150		ms

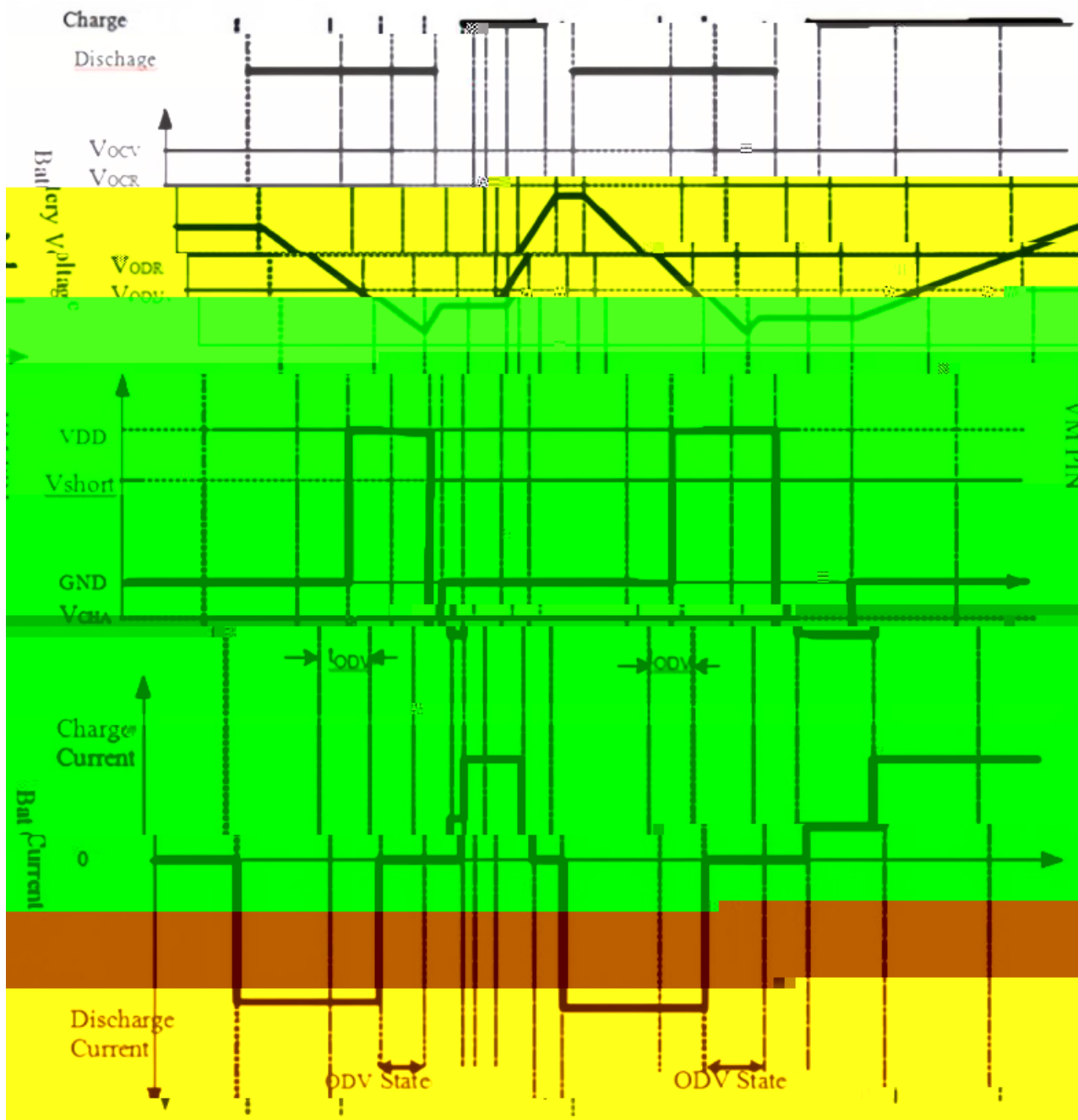
Functionl Block Diagram



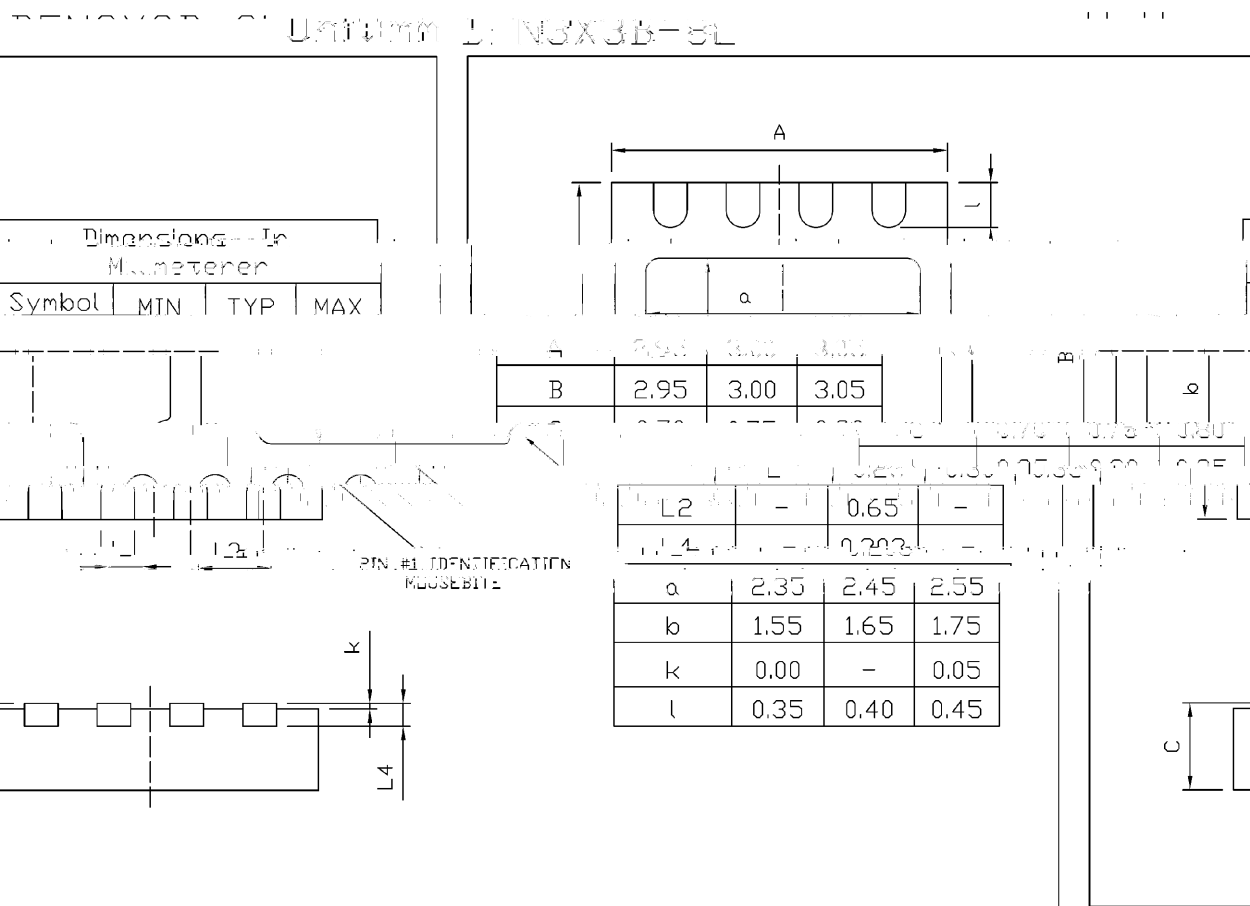
× 5 é	Functional Description
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• } ¢ Timing Chart

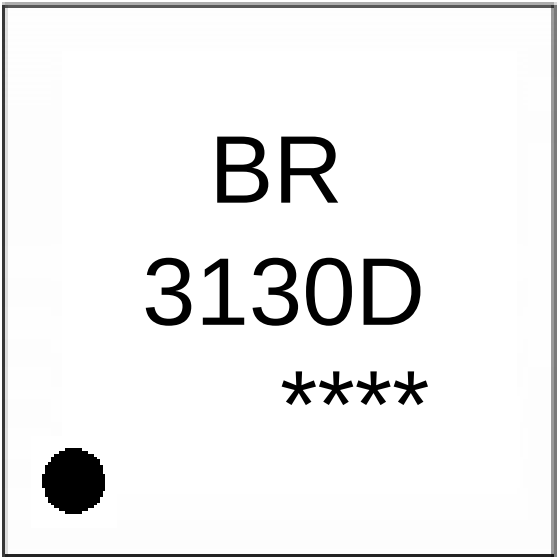
Ú Z ` Ñ Ô ` n V € Overdischarge ` Charging ` Normal Operation.



Ø ± =) ♂ / Package Dimensions



, M y f / Marking Instructions



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